Dual N-Channel Enhancement Mode MOSFET

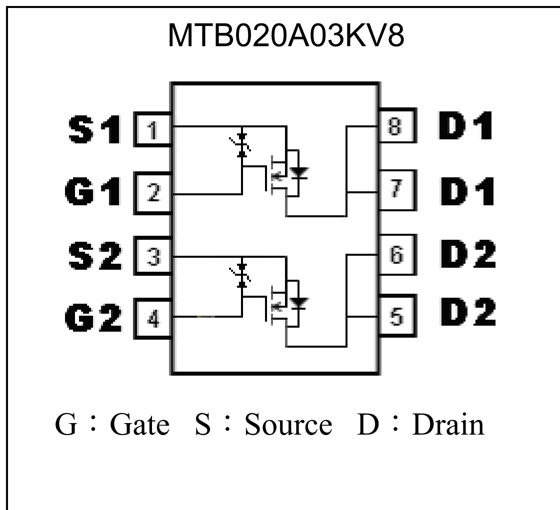
MTB020A03KV8

BV_{DSS}	30V
I_D@V_{GS}=10V, T_A=25˚C	6.6A
I_D@V_{GS}=10V, T_C=25˚C	12A
R_{DSON}@V_{GS}=10V typ.	15.2 mΩ
R_{DSON}@V_{GS}=4.5V typ.	20.1 mΩ

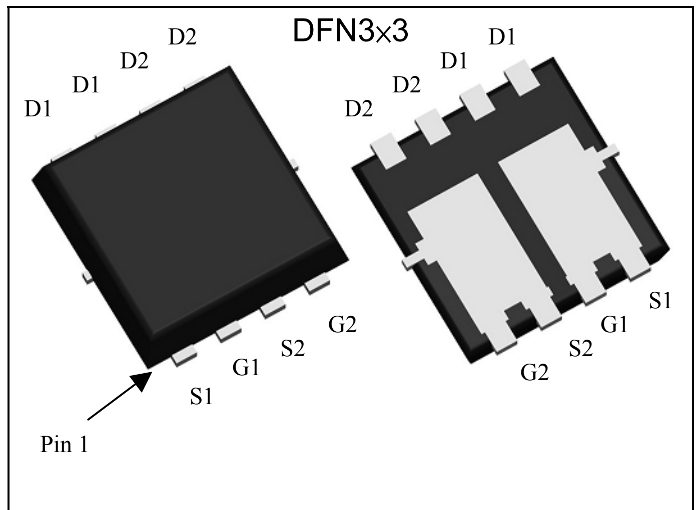
Features

- Simple drive requirement
- Low on-resistance
- Fast switching speed
- Pb-free lead plating and halogen-free package

Equivalent Circuit

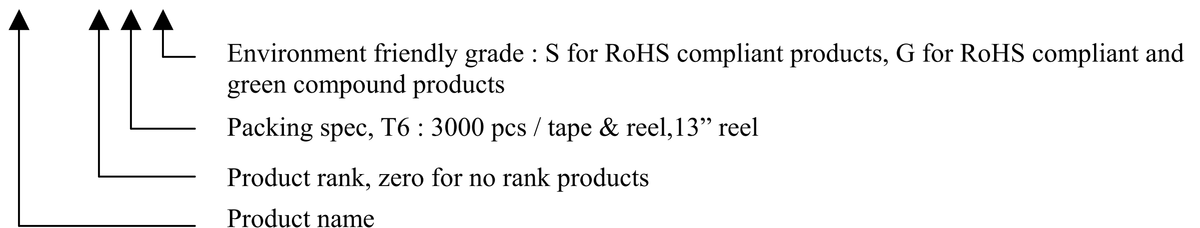


Outline



Ordering Information

Device	Package	Shipping
MTB020A03KV8-0-T6-G	DFN3x3 (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel



Absolute Maximum Ratings (T_C=25°C, unless otherwise noted)

Parameter		Symbol	Limits	Unit
Drain-Source Breakdown Voltage		BV_{DSS}	30	V
Gate-Source Voltage		V_{GS}	±16	
Continuous Drain Current *2	T_A=25 °C, V_{GS}=10V	I_{DSM}	6.6	A
	T_A=70 °C, V_{GS}=10V		5.3	
Continuous Drain Current	T_C=25 °C, V_{GS}=10V	I_D	12	
	T_C=100 °C, V_{GS}=10V		7.6	
Pulsed Drain Current * 3		I_{DM}	48	
Total Power Dissipation	T_A=25°C, Single device operation	P_{DSM}	1.5 *2	W
	T_A=70°C, Single device operation		0.96 *2	
	T_A=25°C,Single device value at dual operation		1.24 *2	
	T_A=70°C,Single device value at dual operation		0.79 *2	
	T_C=25°C	P_D * 1	5	
	T_C=100°C		2	
Operating Junction and Storage Temperature Range		Tj; Tstg	-55~+150	°C

Thermal Data

Parameter	Symbol	Value	Unit
Max. Thermal Resistance, Junction-to-ambient, single device operation	$R_{th,j-a}$	84 *2	°C/W
Max. Thermal Resistance, Junction-to-ambient, single device value at dual operation		101 *2	
Max. Thermal Resistance, Junction-to-case	$R_{th,j-c}$	25	

Note : 1.The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

2. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in²FR-4 board with 2 oz. copper, in a still air environment with T_A=25°C, t≤5s. 216°C/W when mounted on a minimum pad of 2 oz. copper. The power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
3. Pulse width limited by junction temperature $T_{J(MAX)}$=150°C. Ratings are based on low duty cycles to keep initial T_J=25°C.

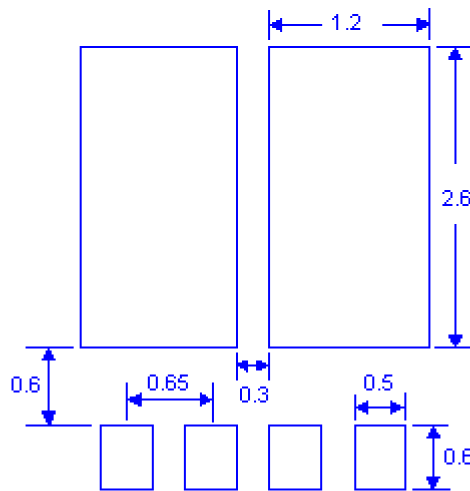
N-Channel Electrical Characteristics (T_C=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV_{DSS}	30	-	-	V	V_{GS}=0V, I_D=250μA
$V_{GS(th)}$	1	-	2.5		V_{DS}=V_{GS}, I_D=250μA
I_{GSS}	-	-	±10	μA	V_{GS}=±16V, V_{DS}=0V
I_{DSS}	-	-	1		V_{DS}=30V, V_{GS}=0V
	-	-	10		V_{DS}=24V, V_{GS}=0V, Tj=70°C
*$R_{DS(ON)}$	-	15.2	20	mΩ	V_{GS}=10V, I_D=10A
	-	20.1	28		V_{GS}=4.5V, I_D=8A
*G_{FS}	-	3.6	-	S	V_{DS}=10V, I_D=1A

Dynamic					
Ciss	-	438	-	pF	V_{DS}=25V, V_{GS}=0V, f=1MHz
Coss	-	63	-		
Crss	-	47	-		
*$t_{d(ON)}$	-	5.8	-	ns	V_{DS}=15V, I_D=1A, V_{GS}=10V, R_G=6Ω
*t_r	-	17.2	-		
*$t_{d(OFF)}$	-	33.8	-		
*t_f	-	10.4	-		
*Qg	-	12.1	-	nC	V_{DS}=24V, I_D=10A, V_{GS}=10V
*Qgs	-	1.7	-		
*Qgd	-	3.6	-		
Body Diode					
*V_{SD}	-	0.8	1.2	V	V_{GS}=0V, I_S=2.3A
*trr	-	9.2	-	ns	I_S=2.3A, V_{GS}=0V, dI/dt=100A/μs
*Qrr	-	4	-	nC	

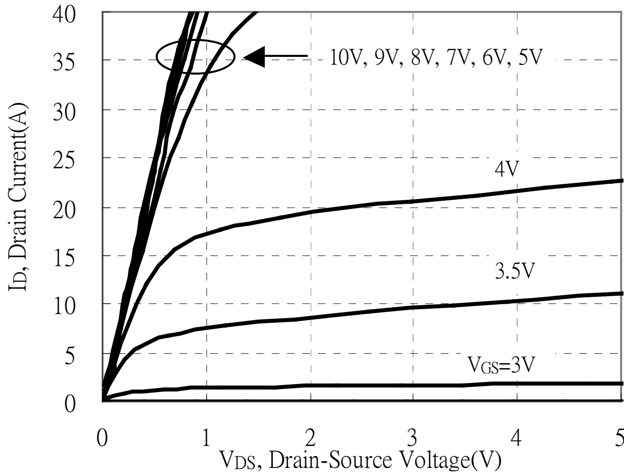
*Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

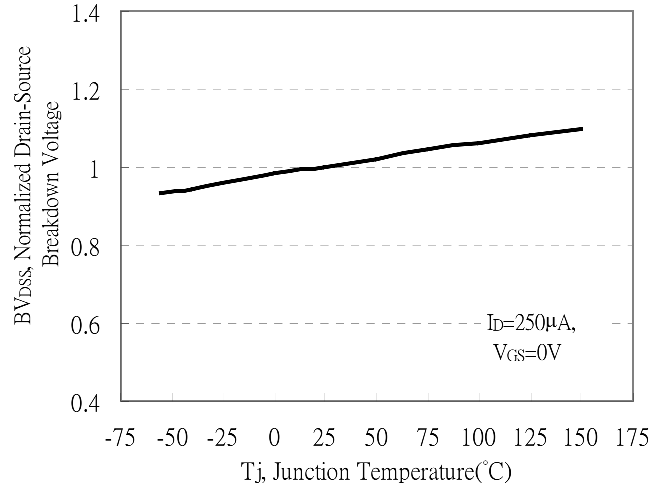
Recommended Soldering Footprint

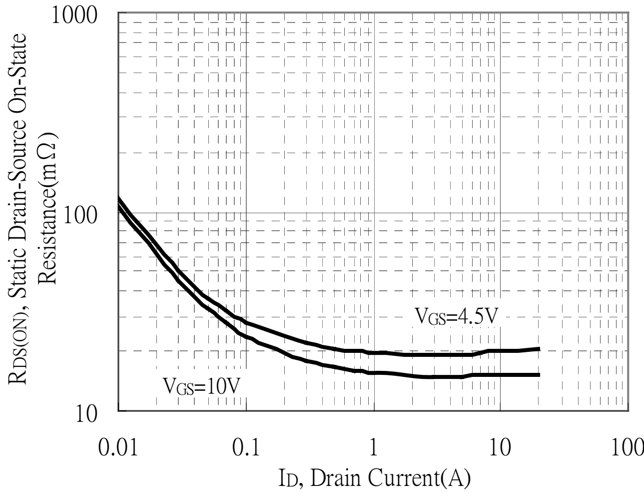


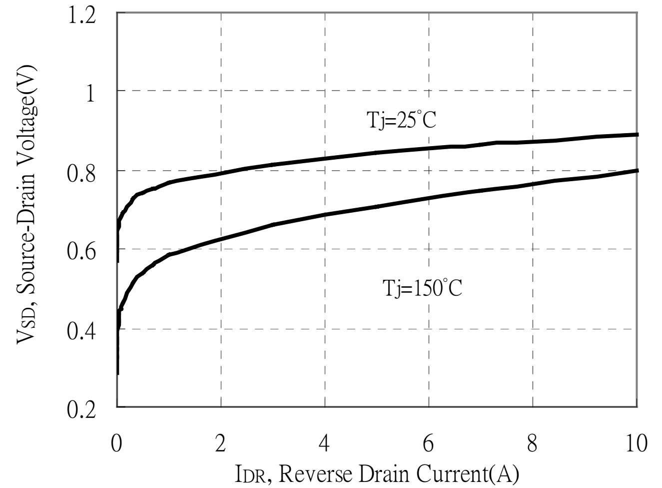
unit : mm

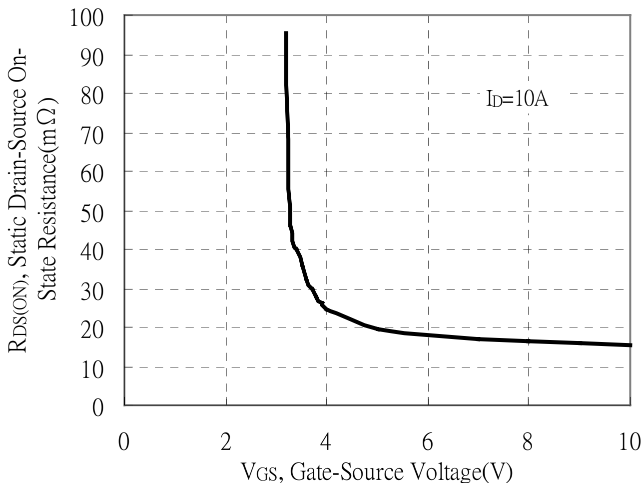
Typical Characteristics :

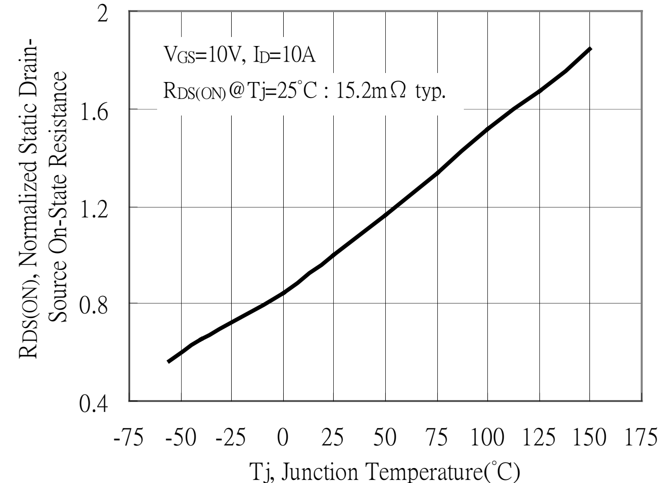












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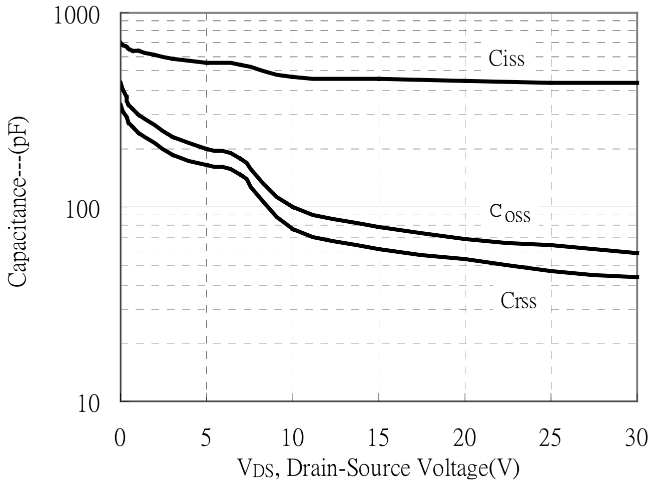
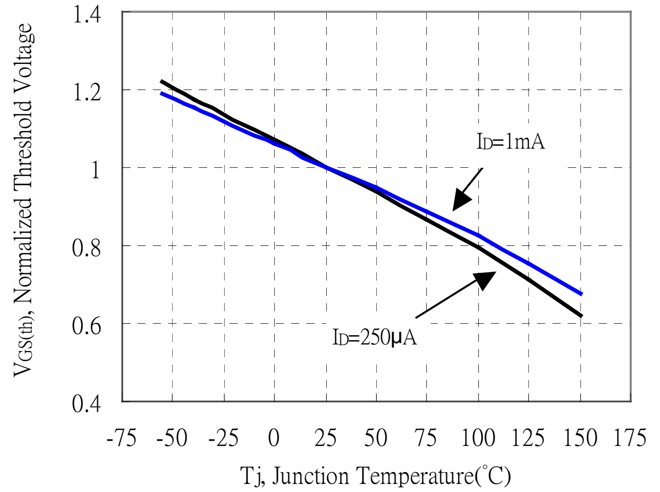
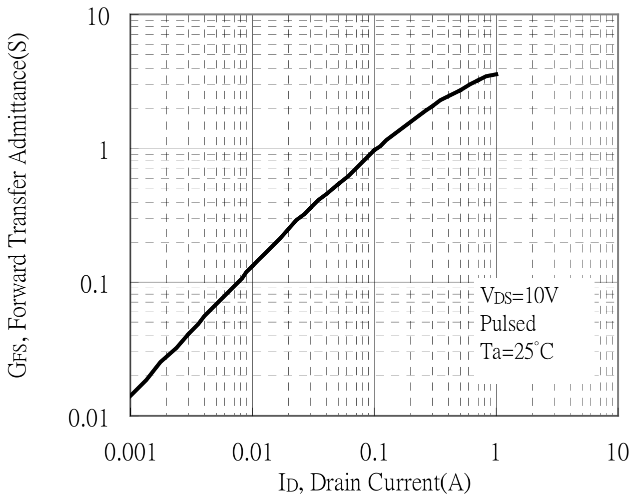
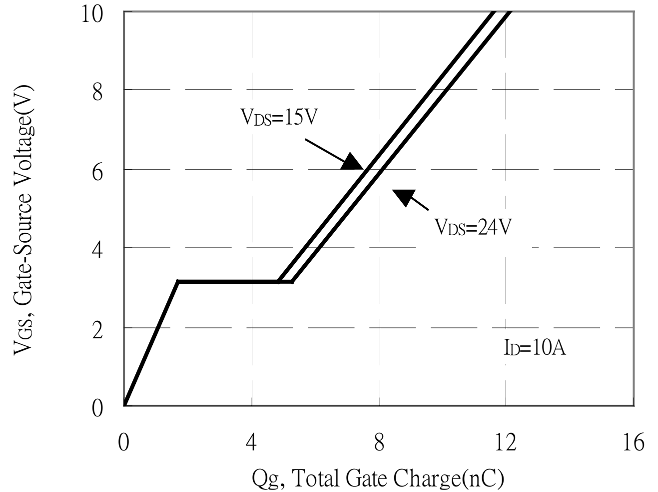
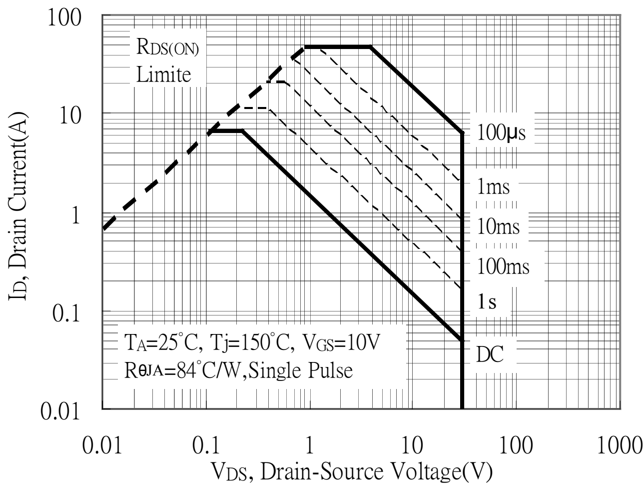
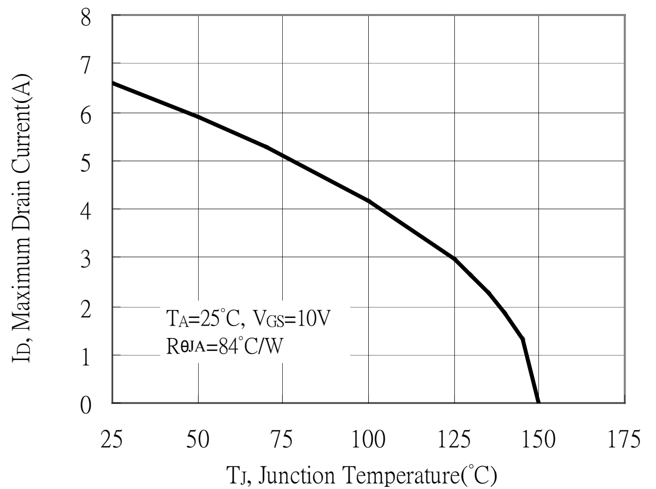




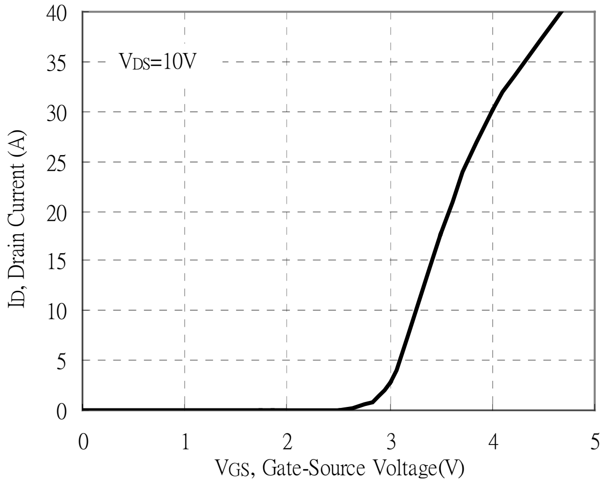


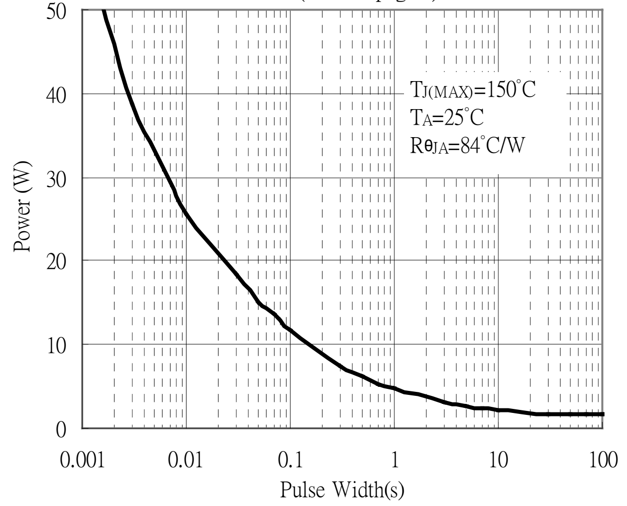


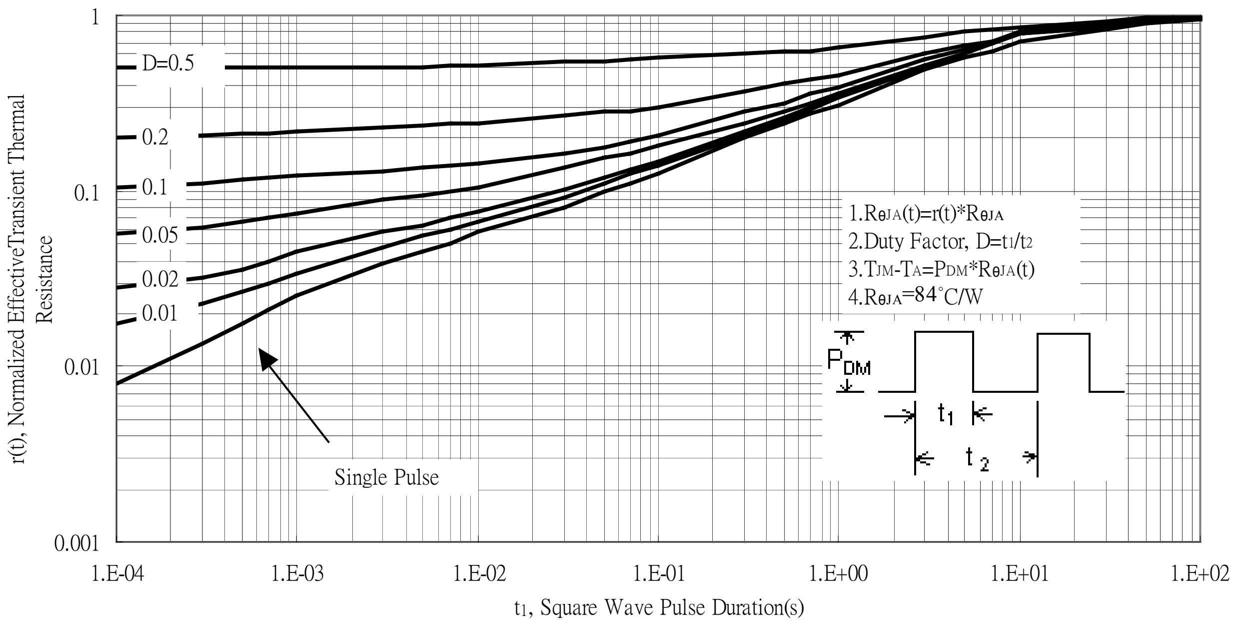




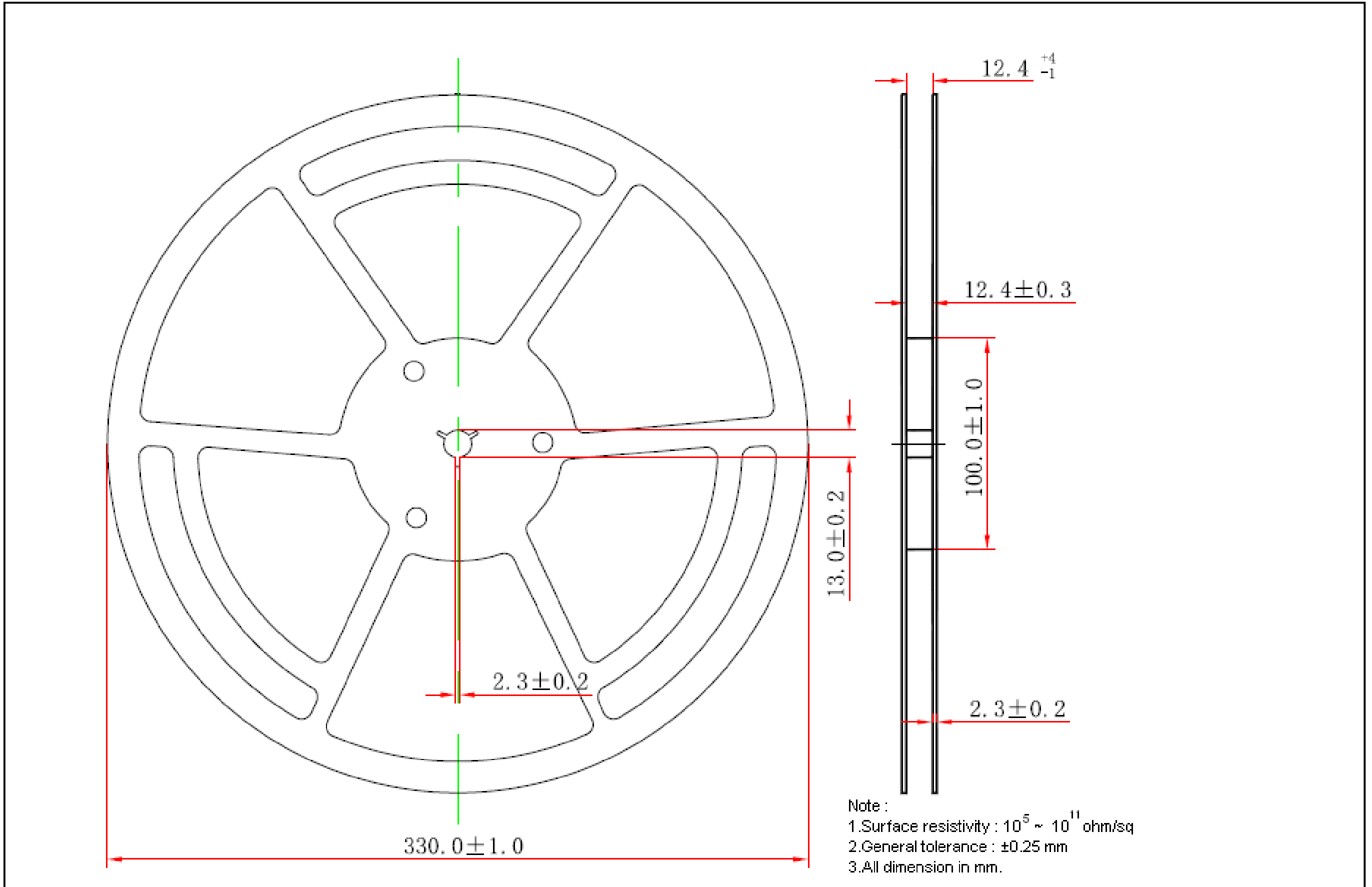
Typical Characteristics(Cont.) :



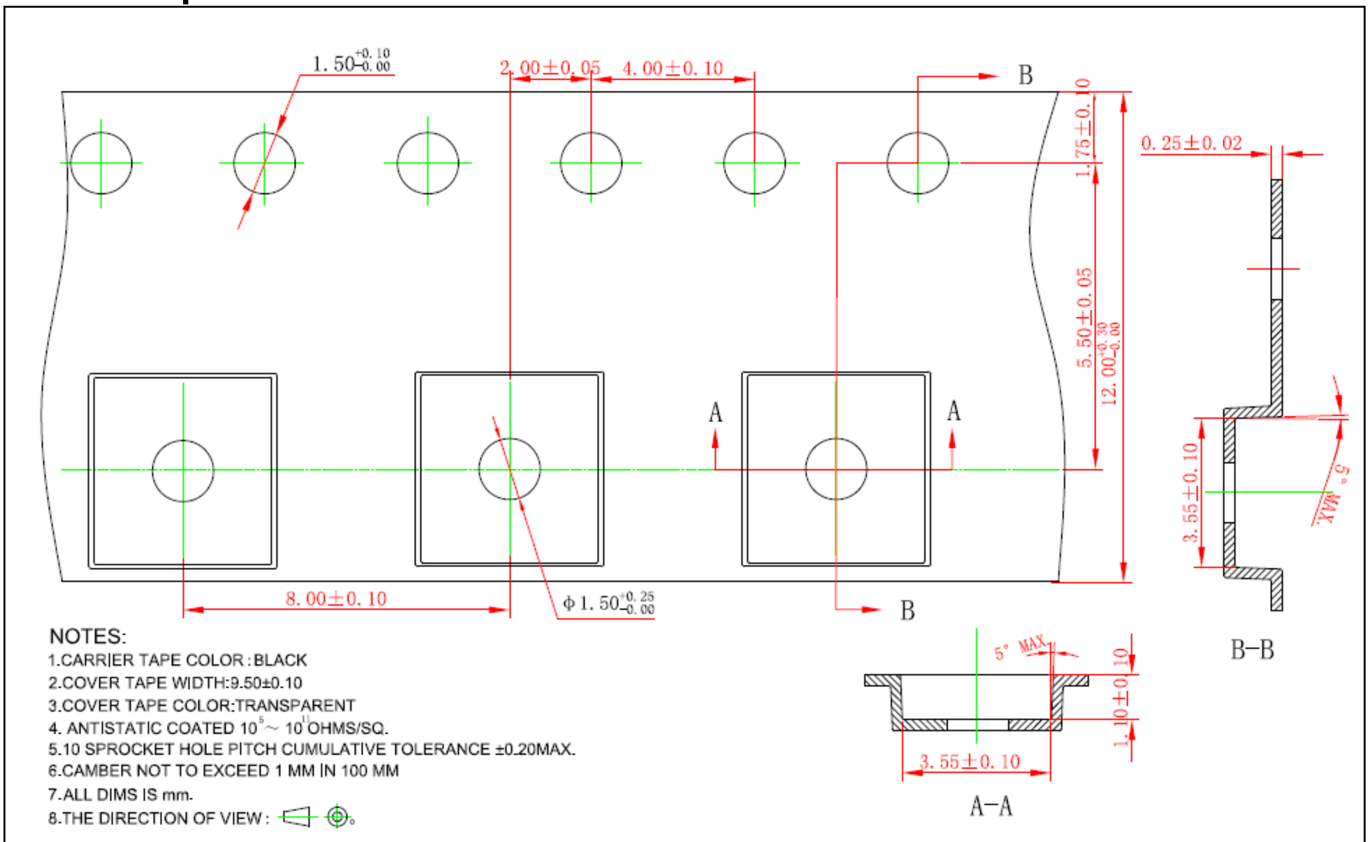




Reel Dimension



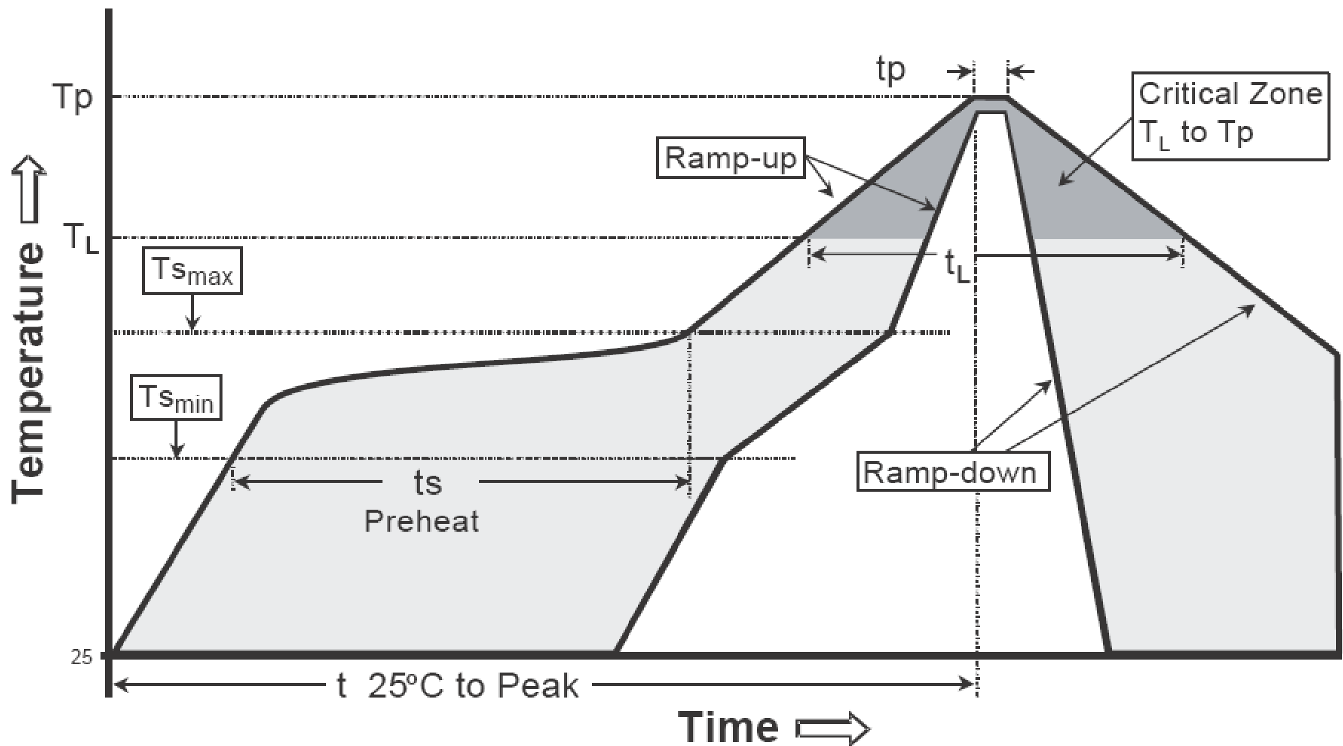
Carrier Tape Dimension



Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

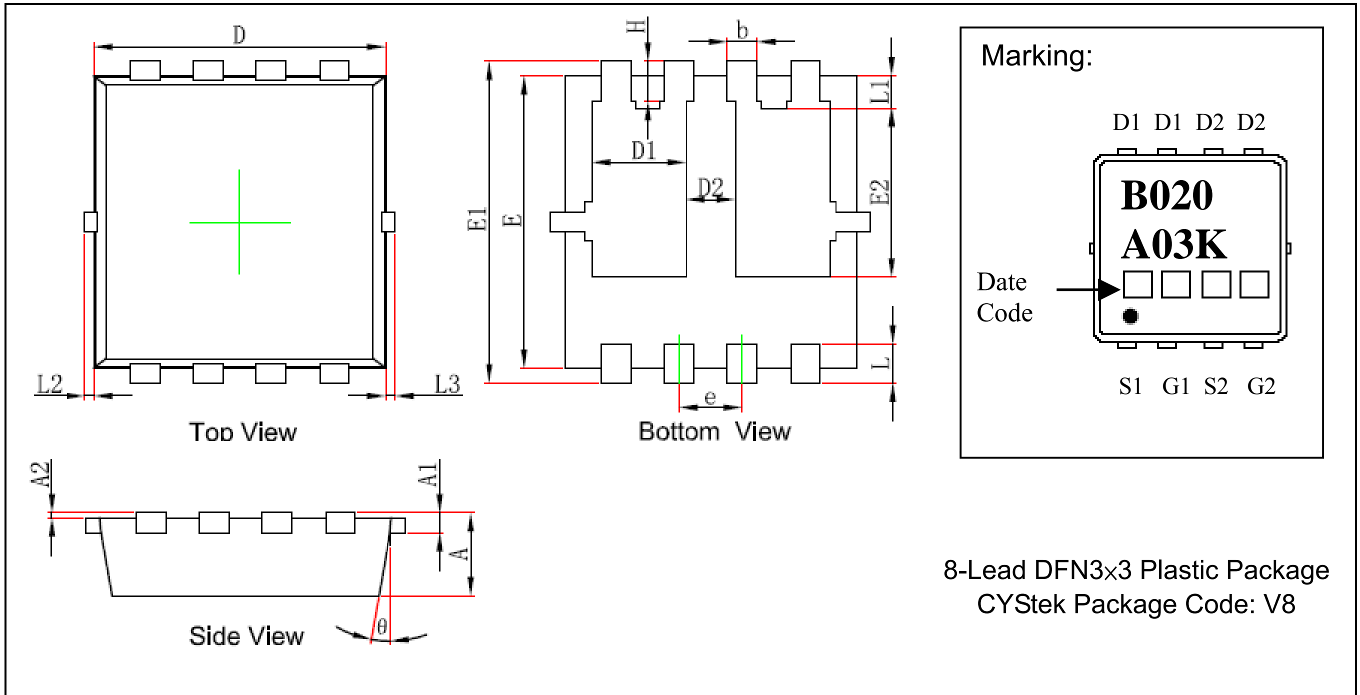
Recommended temperature profile for IR reflow



Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (Tsmax to Tp)	3°C/second max.	3°C/second max.
Preheat −Temperature Min(T_S min) −Temperature Max(T_S max) −Time(ts_{min} to ts_{max})	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: −Temperature (T_L) − Time (t_L)	183°C 60-150 seconds	217°C 60-150 seconds
Peak Temperature(T_P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(tp)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

DFN3x3 Dimension



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.650	0.850	0.026	0.033	b	0.200	0.400	0.008	0.016
A1	0.152 REF		0.006 REF		e	0.550	0.750	0.022	0.030
A2	0.000	0.050	0.000	0.002	L	0.300	0.500	0.012	0.020
D	2.900	3.100	0.114	0.122	L1	0.180	0.480	0.007	0.019
D1	0.935	1.135	0.037	0.045	L2	0.000	0.100	0.000	0.004
D2	0.280	0.480	0.011	0.019	L3	0.000	0.100	0.000	0.004
E	2.900	3.100	0.114	0.122	H	0.315	0.515	0.012	0.020
E1	3.150	3.450	0.124	0.136	θ	9°	13°	9°	13°
E2	1.535	1.935	0.060	0.076					

Notes: 1.Controlling dimension: millimeters.
2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead: pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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